

BULT118

High voltage fast-switching NPN power transistor

Features

- High voltage capability
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed

Applications

- Electronic ballast for fluorescent lighting
- Flyback and forward single transistor low power converters

Description

The device is manufactured using high voltage multi-epitaxial planar technology for high switching speeds and medium voltage capability.

It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA.

The device is designed for use in lighting applications and low cost switch-mode power supplies.

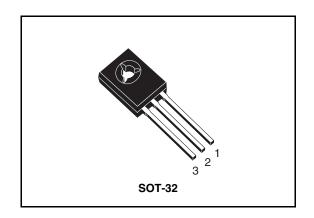


Figure 1. Internal schematic diagram

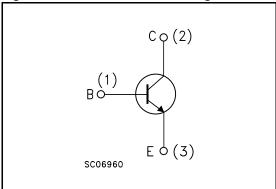


Table 1. Device summary

Order code	Marking	Package	Packaging
BULT118	BULT118	SOT-32	Tube

July 2008 Rev 2 1/10

Electrical ratings BULT118

1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{BE} = 0)	700	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	400	V
V _{EBO}	Emitter-base voltage (I _C = 0)	9	V
I _C	Collector current	2	Α
I _{CM}	Collector peak current (t _P < 5 ms)	4	Α
I _B	Base current	1	Α
I _{BM}	Base peak current (t _P < 5 ms)	2	Α
P _{tot}	Total dissipation at T _c = 25 °C	45	W
T _{stg}	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$

Table 3. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current	V _{CE} = 700 V			100	μΑ
	(V _{BE} =0)	V _{CE} = 700 V T _C = 125 °C			500	μΑ
I _{CEO}	Collector-emitter leakage current	V _{CE} = 400 V			250	μА
V_{EBO}	Emitter-base voltage	I _E = 10 mA	9			V
V _{CEO(sus)} (1)	Collector-emitter sustaining voltage (I _B = 0)	I _C = 10 mA	400			V
		$I_C = 0.5 \text{ A}$ $I_B = 0.1 \text{ A}$			0.5	V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$I_C = 1 A$ $I_B = 0.2 A$			1	V
		$I_C = 2 A$ $I_B = 0.4 A$			1.5	V
	D	I _C = 0.5 A I _B = 0.1 A			1	V
V _{BE(sat)} (1)	Base-emitter saturation voltage	$I_C = 1 A$ $I_B = 0.2 A$			1.2	V
		$I_C = 2 A$ $I_B = 0.4 A$			1.3	V
		$I_C = 10 \text{ mA}$ $V_{CE} = 5 \text{ V}$	10			
h _{FE} ⁽¹⁾	DC current gain	$I_C = 0.5 \text{ A}$ $V_{CE} = 5 \text{ V}$	10		50	
		$I_C = 2 A$ $V_{CE} = 5 V$	8			
	Resistive load					
t _r	Rise time	$I_C = 1 \text{ A}$ $V_{CC} = 125 \text{ V}$		0.4	0.7	μS
t _s	Storage time	$I_{B1} = -I_{B2} = 0.2 \text{ A}$		3.2	4.5	μS
t _f	Fall time			0.25	0.4	μS
	Inductive load	I _C = 1 A I _{B1} = 0.2 A				
t _s	Storage time	$V_{BE(off)} = -5 \text{ V}$ L= 50 mH		0.8		μS
t _f	Fall time	V _{Clamp} = 300 V		0.16		μS

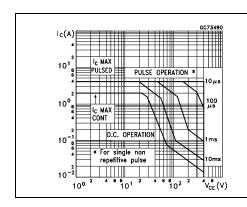
^{1.} Pulsed duration = 300 μ s, duty cycle \leq 1.5 %

Electrical characteristics BULT118

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Derating curve



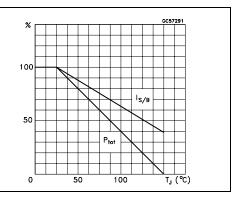
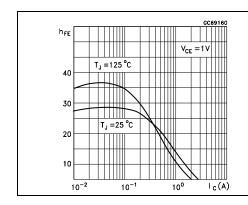


Figure 4. DC current gain

Figure 5. DC current gain



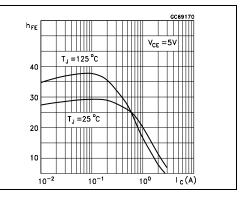
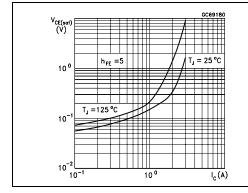
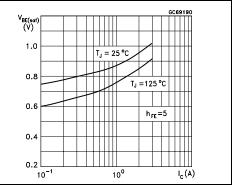


Figure 6. Collector-emitter saturation voltage

Figure 7. Base-emitter saturation voltage

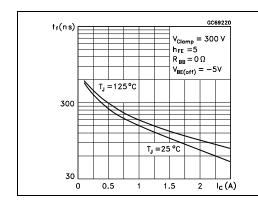




BULT118 Electrical characteristics

Figure 8. Inductive load fall time

Figure 9. Inductive load storage time



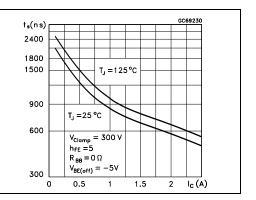
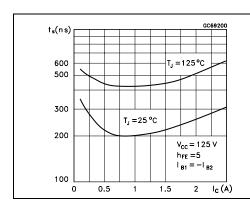


Figure 10. Resistive load fall time

Figure 11. Resistive load storage time



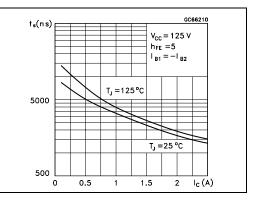
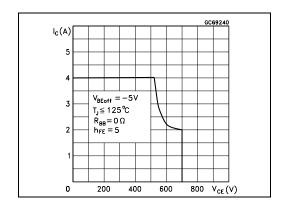


Figure 12. Reverse biased SOA



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2.2 Test circuits

Figure 13. Resistive load switching test circuit

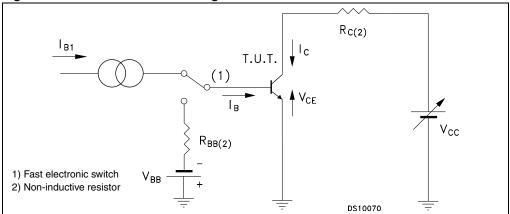
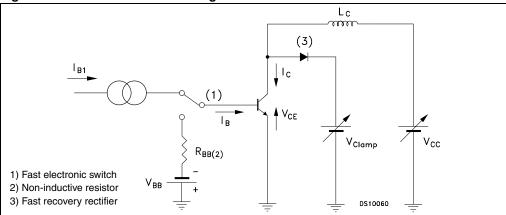


Figure 14. Inductive load switching test circuit

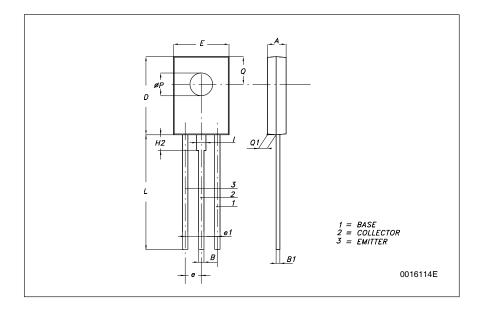


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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	mm.			
DIM.	MIN.	ТҮР	MAX.	
Α	2.4		2.9	
В	0.64		0.88	
B1	0.39		0.63	
D	10.5		11.05	
Е	7.4		7.8	
е	2.04	2.29	2.54	
e1	4.07	4.58	5.08	
L	15.3		16	
Р	2.9		3.2	
Q		3.8		
Q1	1		1.52	
H2		2.15		
I		1.27		



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BULT118 Revision history

4 Revision history

Table 4. Document revision history

Date	Revision	Changes	
29-Sep-2003	1	Initial release.	
10-Jul-2008	2	2 Updated: V _{CEO(sus)} condition in <i>Table 3 on page 3</i> , SOT-32 mechanical data, cover page	

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